

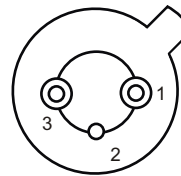
High-speed photodiode

Features of Diode

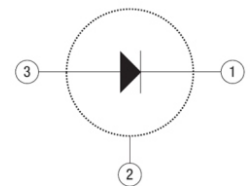
- SI PIN photodiode
- High speed response: 1 GHz ($V_R=3.3$ V)
- High sensitivity
- High reliability



PINOUT



Bottom view



Functional Schematic

Absolute maximum ratings

Parameter	Min.	Max.
Storage temperature	-55 °C	125 °C
Operating temperature	-40 °C	100 °C
Reverse voltage		20 V

Number	Function
1	Cathode
2	Case
3	Anode

Electrical-optical characteristics

Parameter Laser Diode	Test Condition	Min.	Typ.	Max.
Active area diameter			0.4 mm	
Sensitivity	= 780 nm		0.51 A/W	
Dark current	$V_R = 3.3$ V		0.001 nA	0.1 nA
Detection range		320nm	760 nm	1000 nm
Rise time			0.25 ns	
Fall time			0.8 ns	
NEP in $W/Hz^{1/2}$	$V_R = 3.3$ V		1.1×10^{-15}	
Possible receptacle (type A)	ST1, ST2, ST4, P2, LC, SC, FC1, FC2, Fiberdip, SMA1, SMA2			

Compliant with RoHS-requirements (2002/95/EG vom 27.01.2003)

Note: The above product specifications are subject to change without notice.